74AUP2G240

Low-power dual inverting buffer/line driver; 3-state Rev. 02 — 22 February 2008 Produ

Product data sheet

General description

The 74AUP2G240 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS-compatible TTL families.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP2G240 provides the dual inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A HIGH level at pin nOE causes the output to assume a high-impedance OFF-state.

This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input nOE is HIGH.

Features 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V) ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114D Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low-noise overshoot and undershoot < 10 % of V_{CC}
- Input-disable feature allows floating input conditions



- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

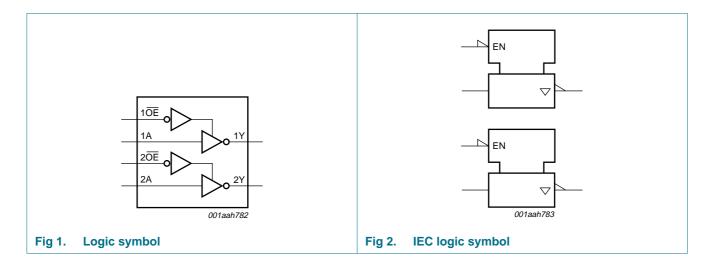
Type number	Package							
	Temperature range	Name	Description	Version				
74AUP2G240DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				
74AUP2G240GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1				
74AUP2G240GM	–40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-1				

4. Marking

Table 2. Marking codes

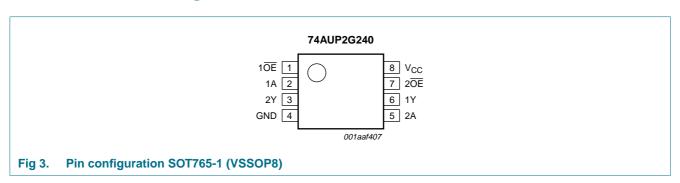
Type number	Marking code
74AUP2G240DC	p40
74AUP2G240GT	p40
74AUP2G240GM	p40

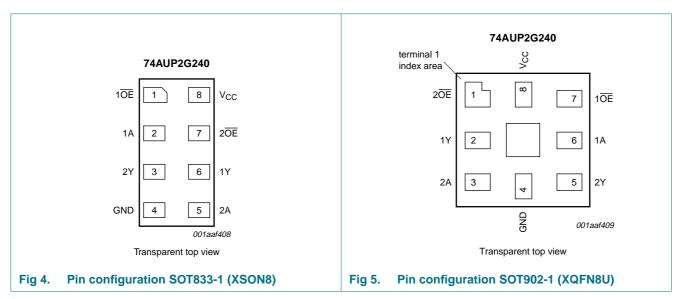
5. Functional diagram



6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description		
	SOT765-1, SOT833-1	SOT902-1			
1 OE	1	7	output enable input 1OE (active LOW)		
1A	2	6	data input 1A		
2Y	3	5	data output 2Y		
GND	4	4	ground (0 V)		
2A	5	3	data input 2A		
1Y	6	2	data output 1Y		
2 OE	7	1	output enable input 2OE (active LOW)		
V _{CC}	8	8	supply voltage		

7. Functional description

Table 4. Function table[1]

Input C		Output
nOE	nA	nY
L	L	Н
L	Н	L
Н	X	Z

^[1] H = HIGH voltage level;

L = LOW voltage level;

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-	-50	mΑ
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mΑ
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V to V_{CC}$	-	±20	mΑ
I _{CC}	supply current		-	50	mΑ
I _{GND}	ground current		-	-50	mΑ
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0 \text{ V}$	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

X = don't care;

Z = high-impedance OFF-state.

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K. For XSON8 and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V _{CC} - 0.1	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ

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Product data sheet

Low-power dual inverting buffer/line driver; 3-state

Static characteristics ...continued Table 7.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1]	-	-	40	μΑ
		$n\overline{OE}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1]	-	-	110	μΑ
		disabled inputs; V_I = GND to 3.6 V; $n\overline{OE}$ = V_{CC} ; V_{CC} = 0.8 V to 3.6 V		-	-	1	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}		-	0.6	-	pF
Co	output capacitance	output enabled; $V_O = GND$; $V_{CC} = 0 V$		-	1.7	-	pF
		output disabled; V_{CC} = 0 V to 3.6 V; V_O = GND or V_{CC}		-	1.5	-	pF
T _{amb} = -	40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$		$0.70 \times V_{\text{CC}}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$		$0.65 \times V_{\text{CC}}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V		1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$		-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$		-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V		$V_{CC}-0.1$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7 \text{ mA}$; $V_{CC} = 1.4 \text{ V}$		1.03	-	-	V
		$I_O = -1.9 \text{ mA}$; $V_{CC} = 1.65 \text{ V}$		1.30	-	-	V
		$I_O = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.97	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.67	-	-	V
		$I_O = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$		2.55	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V		-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		-	-	$0.3\times V_{\text{CC}}$	V
		$I_O = 1.7 \text{ mA}$; $V_{CC} = 1.4 \text{ V}$		-	-	0.37	V
		$I_O = 1.9 \text{ mA}$; $V_{CC} = 1.65 \text{ V}$		-	-	0.35	V
		$I_O = 2.3 \text{ mA}$; $V_{CC} = 2.3 \text{ V}$		-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.45	V
l _l	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V		-	-	±0.5	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V		-	-	±0.5	μΑ

Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V		-	-	±0.6	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V		-	-	0.9	μΑ
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	<u>[1]</u>	-	-	50	μΑ
		$n\overline{OE}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	<u>[1]</u>	-	-	120	μΑ
		disabled inputs; V_I = GND to 3.6 V; $n\overline{OE}$ = V_{CC} ; V_{CC} = 0.8 V to 3.6 V		-	-	1	μΑ
T _{amb} = -	40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V		$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V		$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V		1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V		-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V		-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V		-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V		-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V		$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.30	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V		-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V		-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.50	V
l _l	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V		-	-	±0.75	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	μΑ
l _{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V		-	-	±0.75	μΑ

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Low-power dual inverting buffer/line driver; 3-state

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	[1] -	-	75	μΑ
		$n\overline{OE}$ input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	180	μΑ
		disabled inputs; V_I = GND to 3.6 V; $n\overline{OE}$ = V_{CC} ; V_{CC} = 0.8 V to 3.6 V	-	-	1	μΑ

^[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C		-4	0 °C to +	125 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 p$	F						'	•	'	
t _{pd}	propagation delay	nA to nY; see Figure 6	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	22.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.0	5.8	12.6	2.8	14.1	15.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	4.0	7.3	2.1	8.5	9.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	3.2	5.5	1.9	6.7	7.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	2.6	4.1	1.5	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.4	2.3	3.6	1.3	4.1	4.6	ns
t _{en}	enable time	nOE to nY; see Figure 7	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	70.2	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.1	6.4	14.3	2.8	15.9	17.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.5	4.4	8.1	2.2	9.5	10.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	3.6	6.2	1.9	7.4	8.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	2.8	4.6	1.7	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.7	2.5	4.0	1.7	4.7	5.3	ns
t _{dis}	disable time	nOE to nY; see Figure 7	[4]							
		$V_{CC} = 0.8 \text{ V}$		-	14.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.0	4.3	7.4	2.3	8.3	9.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.6	3.2	5.2	1.7	5.9	6.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.5	3.0	4.8	1.5	5.5	6.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.1	2.2	3.5	1.4	4.0	4.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.3	2.5	3.9	1.4	4.5	5.0	ns

–40 °C to +125 °C

Unit

Symbol Parameter

Low-power dual inverting buffer/line driver; 3-state

25 °C

Table 8. Dynamic characteristics ...continued Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 8.

Conditions

 $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$

 $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$

 $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$

 $V_{CC} = 0.8 \text{ V}$

propagation delay nA to nY; see Figure 6

Min Typ[1] Max Min Max Max (85 °C) (125 °C) $C_L = 10 pF$ [2] propagation delay nA to nY; see Figure 6 t_{pd} $V_{CC} = 0.8 \text{ V}$ 25.7 ns $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ 3.5 6.6 14.5 3.2 16.3 18.0 ns $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ 2.2 4.6 8.4 2.0 9.9 10.9 ns $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ 2.0 3.8 6.4 1.8 7.7 8.6 ns $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ 4.8 1.7 5.7 6.4 1.8 3.1 ns $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ 1.7 2.8 4.3 1.7 5.0 5.5 ns nOE to nY; see Figure 7 [3] enable time t_{en} $V_{CC} = 0.8 \text{ V}$ _ 74.0 ns $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ 3.6 7.4 16.3 3.2 18.2 20.1 ns $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ 2.3 5.1 9.2 2.1 10.9 12.0 ns $V_{CC} = 1.65 \text{ V}$ to 1.95 V 7.1 1.8 9.4 2.0 4.1 8.5 ns V_{CC} = 2.3 V to 2.7 V 1.8 3.4 5.4 1.7 6.4 7.1 ns $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ 1.8 3.1 4.8 1.7 5.7 6.3 ns nOE to nY; see Figure 7 [4] disable time t_{dis} $V_{CC} = 0.8 \text{ V}$ 33.7 ns $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ 3.4 5.4 9.0 3.2 10.0 11.0 ns 2.1 $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ 2.1 6.3 7.1 7.9 4.1 ns

2.3

1.6

2.1

[2]

4.2

3.0

3.8

29.0

6.3

4.6

5.7

1.8

1.7

1.7

7.1

5.2

6.4

7.9

5.7

7.1

ns

ns

ns

ns

	45	- E
し ∟ =	10	рr

 t_{pd}

		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.9	7.4	16.3	3.6	18.4	20.2	ns
		V_{CC} = 1.4 V to 1.6 V		3.0	5.1	9.4	2.5	11.1	12.3	ns
		V_{CC} = 1.65 V to 1.95 V		2.2	4.2	7.2	2.1	8.7	9.6	ns
		V_{CC} = 2.3 V to 2.7 V		2.0	3.5	5.4	1.9	6.5	7.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.3	4.9	1.9	5.7	6.4	ns
t _{en}	enable time	nOE to nY; see Figure 7	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	77.8	-	-	-	-	ns
		$V_{CC} = 0.8 \text{ V}$ $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.0	77.8 8.2	18.2	3.6	20.4	22.5	ns ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.0	8.2	18.2	3.6	20.4	22.5	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.0 3.0	8.2 5.6	18.2 10.3	3.6 2.5	20.4 12.2	22.5 13.4	ns ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		-40	Unit		
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{dis}	disable time	nOE to nY; see Figure 7	1			•		•	
		$V_{CC} = 0.8 \text{ V}$	-	62.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.3	6.6	10.4	3.6	11.6	12.8	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	5.0	7.4	2.5	8.4	9.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.0	5.3	7.8	2.1	8.7	9.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.1	3.8	5.7	2.0	6.4	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.9	5.0	7.4	1.9	8.3	9.1	ns
C _L = 30	oF								
t _{pd}	propagation delay	nA to nY; see Figure 6	1						
		$V_{CC} = 0.8 \text{ V}$	-	39.1	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	5.0	9.7	21.6	4.6	24.3	26.8	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.0	6.7	12.3	3.0	14.6	16.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.9	5.5	9.5	2.7	11.5	12.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.7	4.6	7.1	2.5	8.6	9.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.6	4.3	6.4	2.5	7.7	8.5	ns
t _{en}	enable time	nOE to nY; see Figure 7	1						
		$V_{CC} = 0.8 \text{ V}$	-	89.4	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	5.2	10.6	23.8	4.6	26.7	29.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.0	7.3	13.2	3.0	15.7	17.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.0	6.0	10.2	2.7	12.3	13.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.8	5.0	7.8	2.6	9.3	10.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.8	4.8	7.1	2.6	8.4	9.3	ns
t _{dis}	disable time	nOE to nY; see Figure 7	<u>·]</u>						
		$V_{CC} = 0.8 \text{ V}$	-	68.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	6.0	9.3	15.0	4.6	16.5	18.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.4	7.7	11.0	3.0	12.2	13.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	5.1	8.8	12.4	2.7	13.7	15.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	3.6	6.2	9.0	2.6	10.0	11.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.2	8.8	12.7	2.6	14.0	15.4	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C		-40	Unit		
			ı	Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
C_{PD}	power dissipation capacitance	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	<u>[5]</u>							
		$V_{CC} = 0.8 \text{ V}$		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.9	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	3.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.2	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.7	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.2	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] t_{en} is the same as t_{PZH} and t_{PZL}.
- [4] t_{dis} is the same as t_{PHZ} and t_{PLZ} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

fo = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms

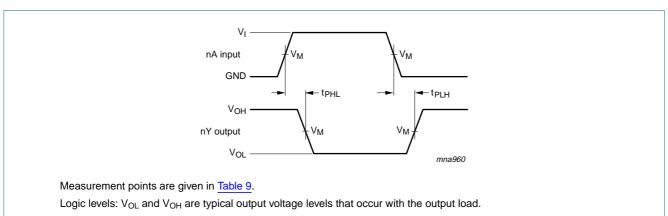


Fig 6. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input					
V _{CC}	V _M	V _M	V _I	$t_r = t_f$			
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{\text{CC}}$	V_{CC}	≤ 3.0 ns			

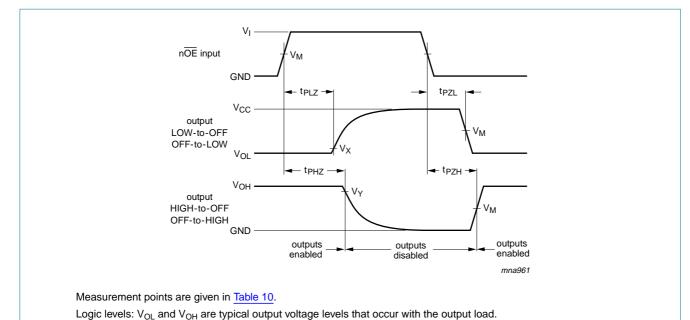


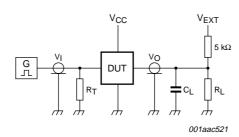
Fig 7. 3-state enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output					
V _{CC}	V _M	V _M	V _X	V _Y			
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.1 V$	V _{OH} – 0.1 V			
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	V _{OH} – 0.15 V			
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 V$	V _{OH} – 0.3 V			

NXP Semiconductors 74AUP2G240

Low-power dual inverting buffer/line driver; 3-state



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuitry for switching times

Table 11. Test data

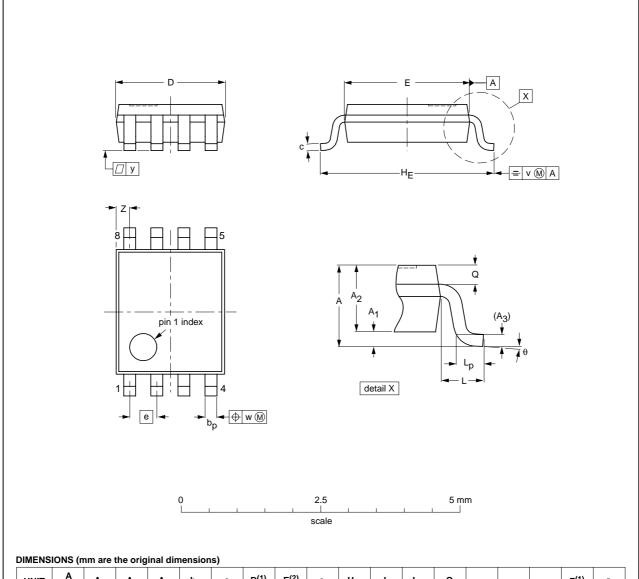
Supply voltage	Load		V _{EXT}			
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$	

[1] For measuring enable and disable times R_L = 5 $k\Omega$, for measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT765-1		MO-187				02-06-07	

Fig 9. Package outline SOT765-1 (VSSOP8)

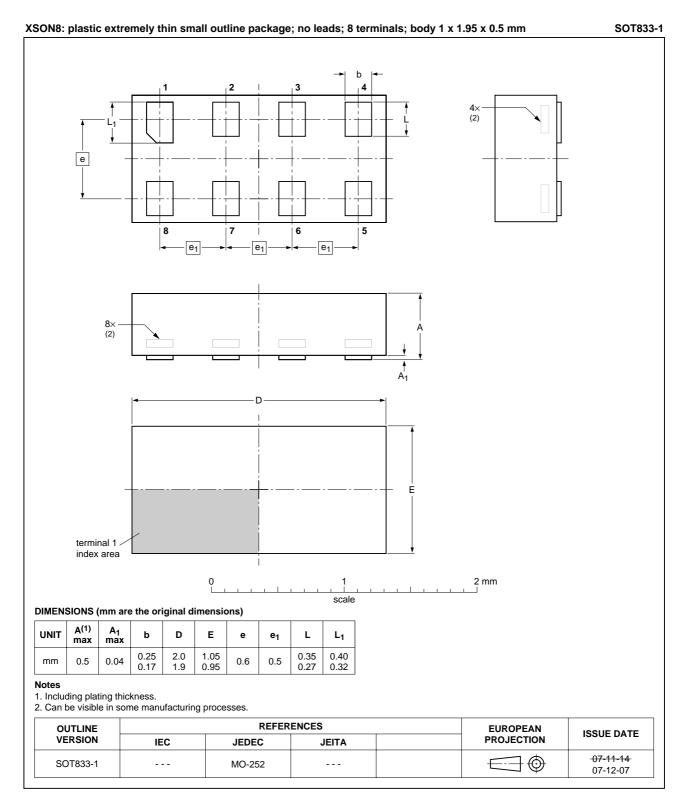


Fig 10. Package outline SOT833-1 (XSON8)

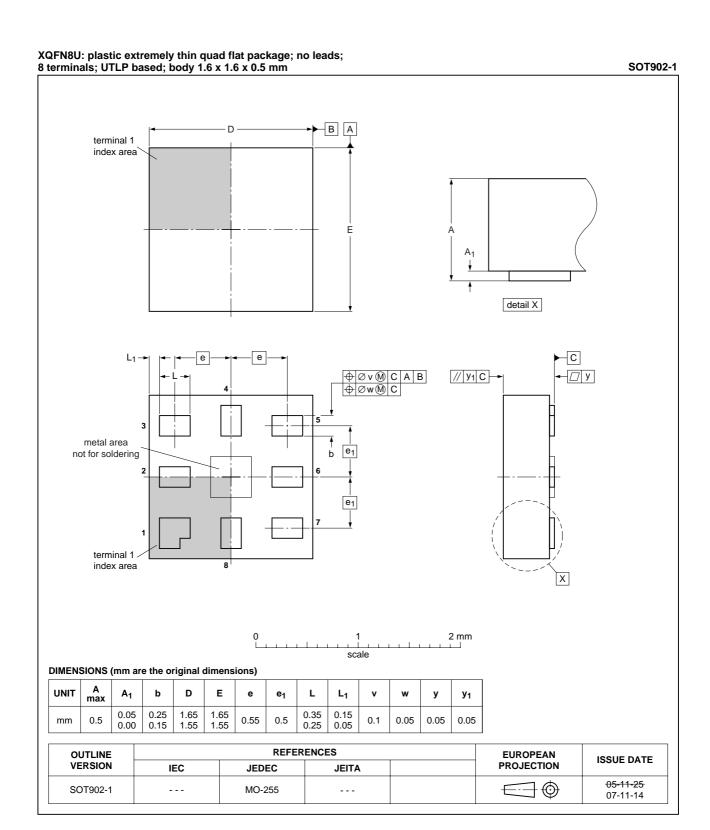


Fig 11. Package outline SOT902-1 (XQFN8U)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
74AUP2G240_2	20080222	Product data sheet	-	74AUP2G240_1			
Modifications: ● Figure 1 and Figure 2: pin numbers removed							
	 Figure 11: package outline drawing updated to latest version 						
74AUP2G240_1	20061006	Product data sheet	-	-			

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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